

	Type	L #	Hits	Search Text	DBs
1	BRS	L1	3004	trench adj capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
2	BRS	L3	112	2 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
3	BRS	L4	3	("6090707" "6140234" "6300201").PN.	USPAT
4	BRS	L5	13	("4396933" "4589928" "4761384" "5081056" "5111270" "5334908" "5422300" "5573837" "5629579" "5920104" "5970362" "5989718" "6037651").PN.	USPAT
5	BRS	L6	1	"5392189".PN.	USPAT
6	BRS	L7	1936	ahn.inv.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
7	BRS	L8	9	7 and (byoung adj kwon)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
8	BRS	L9	3	1 and (conduct\$4 with (ruthenium ru) same (pecvd and lpcvd))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
9	IS&R	L10	24	(""6037219") or ("6144060") or ("5665628") or ("6300191") or ("6323081") or ("6350647") or ("5895250") or ("6184081") or ("6391660") or ("6100139") or ("6046093") or ("6077738")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
10	IS&R	L11	5825	(438/239,240,243,244,253,254,396,397,387).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
11	IS&R	L12	0	("1 and 11").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
12	BRS	L13	549	11 and (trench adj capacitor)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
13	BRS	L14	0	13 and (conduct\$4 with (ruthenium ru) same (pecvd and lpcvd))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
14	BRS	L15	0	13 and (conduct\$4 with (ruthenium ru) with (pecvd and lpcvd))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
15	BRS	L16	0	13 and (conduct\$4 with (ruthenium ru) and (pecvd and lpcvd))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
16	BRS	L18	0	17 and (pecvd and lpcvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Typ	L #	Hits	Search T xt	DBs
17	BRS	L20	7	17 and "39"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
18	BRS	L21	20	("5275974" "5318927" "5330931" "5340370" "5354712" "5392189" "5394000" "5516346" "5527423" "5566045" "5614444" "5627094" "5639697" "5661064" "5691571" "5696017" "5741722" "5786259" "5801079" "5843818").PN.	USPAT
19	BRS	L19	39	13 and (pecvd and lpcvd)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
20	BRS	L17	12	13 and (conduct\$4 with (ruthenium ru))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
21	BRS	L2	131	"2" and (conduct\$4 with (pecvd and lpcvd))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
22	BRS	L22	7	1 and (conduct\$4 with (pecvd and lpcvd))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
23	BRS	L23	2	1 and (conduct\$4 with (pecvd adj4 lpcvd))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
24	BRS	L24	7	1 and (conduct\$4 with (pecvd with lpcvd))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
25	BRS	L25	0	1 and ((pecvd and lpcvd) same chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
26	BRS	L26	0	1 and ((pecvd and lpcvd) and (in adj chamber))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
27	BRS	L27	9	1 and (pecvd and lpcvd and chamber)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
28	BRS	L28	0	1 and (pecvd adj lpcvd) and chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
29	BRS	L29	14	1 and (pecvd or (plasma adj enhanced adj chemical adj vapor adj deposition)) and (lpcvd or (low adj pressure adj chemical adj vapor adj deposition)) and chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
30	IS&R	L30	2	("20020197836") or ("20020142499").PN.	US-PGPUB
31	BRS	L31	1039	(pecvd or (plasma adj enhanced adj chemical adj vapor adj deposition)) and (lpcvd or (low adj pressure adj chemical adj vapor adj deposition)) and chamber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
32	BRS	L32	943	31 and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB

	Typ	L #	Hits	Search Text	DBs
33	BRS	L33	747	32 and conduct\$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB
34	BRS	L34	224	33 and capacitor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB